

TOSHIBA Field Effect Transistor Silicon N Channel MOS Type (L<sup>2</sup>-π-MOSV)

# 2SK2232

Chopper Regulator, DC-DC Converter and Motor Drive Applications

- 4-V gate drive
- Low drain-source ON resistance :  $R_{DS(ON)} = 36 \text{ m}\Omega$  (typ.)
- High forward transfer admittance :  $|Y_{fs}| = 16 \text{ S}$  (typ.)
- Low leakage current :  $I_{DSS} = 100 \mu\text{A}$  (max) ( $V_{DS} = 60 \text{ V}$ )
- Enhancement mode :  $V_{th} = 0.8 \text{ to } 2.0 \text{ V}$  ( $V_{DS} = 10 \text{ V}$ ,  $I_D = 1 \text{ mA}$ )

### Absolute Maximum Ratings (Ta = 25°C)

| Characteristics                                      | Symbol         | Rating     | Unit |   |
|--|----------------|------------|------|---|
| Drain-source voltage                                 | $V_{DSS}$      | 60         | V    |   |
| Drain-gate voltage ( $R_{GS} = 20 \text{ k}\Omega$ ) | $V_{DGR}$      | 60         | V    |   |
| Gate-source voltage                                  | $V_{GSS}$      | $\pm 20$   | V    |   |
| Drain current  | DC (Note 1)    | $I_D$      | 25   | A |
|  | Pulse (Note 1) | $I_{DP}$   | 100  | A |
| Drain power dissipation ( $T_c = 25^\circ\text{C}$ ) | $P_D$          | 35         | W    |   |
| Single pulse avalanche energy (Note 2)               | $E_{AS}$       | 156        | mJ   |   |
| Avalanche current                                    | $I_{AR}$       | 25         | A    |   |
| Repetitive avalanche energy (Note 3)                 | $E_{AR}$       | 3.5        | mJ   |   |
| Channel temperature                                  | $T_{ch}$       | 150        | °C   |   |
| Storage temperature range                            | $T_{stg}$      | -55 to 150 | °C   |   |

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings. Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/Derating Concept and Methods) and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

### Thermal Characteristics

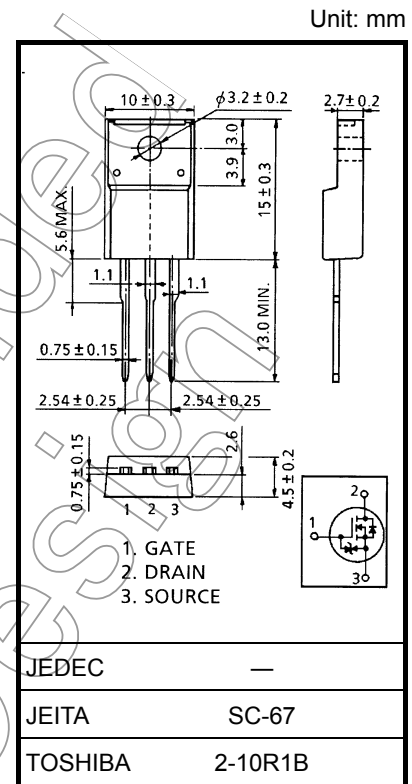
| Characteristics                        | Symbol         | Max  | Unit |
|--|----------------|------|------|
| Thermal resistance, channel to case    | $R_{th(ch-c)}$ | 3.57 | °C/W |
| Thermal resistance, channel to ambient | $R_{th(ch-a)}$ | 62.5 | °C/W |

Note 1: Ensure that the channel temperature does not exceed 150°C.

Note 2:  $V_{DD} = 25 \text{ V}$ ,  $T_{ch} = 25^\circ\text{C}$  (initial),  $L = 339 \mu\text{H}$ ,  $R_G = 25 \Omega$ ,  $I_{AR} = 25 \text{ A}$

Note 3: Repetitive rating: pulse width limited by maximum channel temperature.

This transistor is an electrostatic-sensitive device.  
Please handle with caution.



Weight: 1.9 g (typ.)

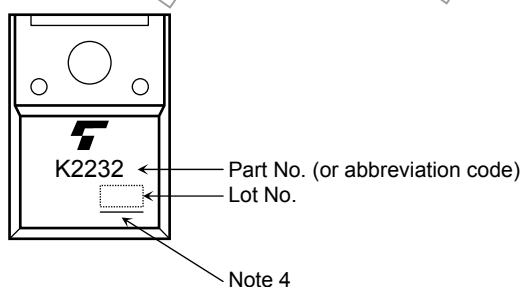
## Electrical Characteristics (Ta = 25°C)

| Characteristics                                 |               | Symbol        | Test Condition   | Min | Typ.  | Max      | Unit          |
|---|---------------|---------------|--|-----|-------|----------|---------------|
| Gate leakage current                            |               | $I_{GSS}$     | $V_{GS} = \pm 16\text{ V}, V_{DS} = 0\text{ V}$  | —   | —     | $\pm 10$ | $\mu\text{A}$ |
| Drain cut-off current                           |               | $I_{DSS}$     | $V_{DS} = 60\text{ V}, V_{GS} = 0\text{ V}$  | —   | —     | 100      | $\mu\text{A}$ |
| Drain-source breakdown voltage                  |               | $V_{(BR)DSS}$ | $I_D = 10\text{ mA}, V_{GS} = 0\text{ V}$  | 60  | —     | —        | V             |
| Gate threshold voltage                          |               | $V_{th}$      | $V_{DS} = 10\text{ V}, I_D = 1\text{ mA}$  | 0.8 | —     | 2.0      | V             |
| Drain-source ON resistance                      |               | $R_{DS(ON)}$  | $V_{GS} = 4\text{ V}, I_D = 12\text{ A}$   | —   | 0.057 | 0.08     | $\Omega$      |
|   |               |               | $V_{GS} = 10\text{ V}, I_D = 12\text{ A}$  | —   | 0.036 | 0.046    |               |
| Forward transfer admittance                     |               | $ Y_{fs} $    | $V_{DS} = 10\text{ V}, I_D = 12\text{ A}$  | 10  | 16    | —        | S             |
| Input capacitance                               |               | $C_{iss}$     | $V_{DS} = 10\text{ V}, V_{GS} = 0\text{ V}, f = 1\text{ MHz}$  | —   | 1000  | —        | pF            |
| Reverse transfer capacitance                    |               | $C_{rss}$     |  | —   | 200   | —        |               |
| Output capacitance                              |               | $C_{oss}$     |  | —   | 550   | —        |               |
| Switching time                                  | Rise time     | $t_r$         | <p><math>I_D = 12\text{ A}</math><br/><math>V_{GS} = 10\text{ V}</math><br/><math>V_{DD} = 30\text{ V}</math><br/><math>R_L = 2.5\ \Omega</math><br/><math>Duty \leq 1\%, t_w = 10\ \mu\text{s}</math></p> | —   | 20    | —        | ns            |
|   | Turn-on time  | $t_{on}$      |  | —   | 30    | —        |               |
|   | Fall time     | $t_f$         |  | —   | 55    | —        |               |
|   | Turn-off time | $t_{off}$     |  | —   | 130   | —        |               |
| Total gate charge (Gate-source plus gate-drain) |               | $Q_g$         | $V_{DD} = 48\text{ V}, V_{GS} = 10\text{ V}, I_D = 25\text{ A}$  | —   | 38    | —        | nC            |
| Gate-source charge                              |               | $Q_{gs}$      |  | —   | 25    | —        |               |
| Gate-drain ("miller") charge                    |               | $Q_{gd}$      |  | —   | 13    | —        |               |

## Source-Drain Ratings and Characteristics (Ta = 25°C)

| Characteristics                           | Symbol    | Test Condition  | Min | Typ. | Max  | Unit          |
|---|-----------|---|-----|------|------|---------------|
| Continuous drain reverse current (Note 1) | $I_{DR}$  | —   | —   | —    | 25   | A             |
| Pulse drain reverse current (Note 1)      | $I_{DRP}$ | —   | —   | —    | 100  | A             |
| Forward voltage (diode)                   | $V_{DSF}$ | $I_{DR} = 25\text{ A}, V_{GS} = 0\text{ V}$                                       | —   | —    | -1.8 | V             |
| Reverse recovery time                     | $t_{rr}$  | $I_{DR} = 25\text{ A}, V_{GS} = 0\text{ V}, dI_{DR}/dt = 50\text{ A}/\mu\text{s}$ | —   | 50   | —    | ns            |
| Reverse recovered charge                  | $Q_{rr}$  |   | —   | 35   | —    | $\mu\text{C}$ |

## Marking

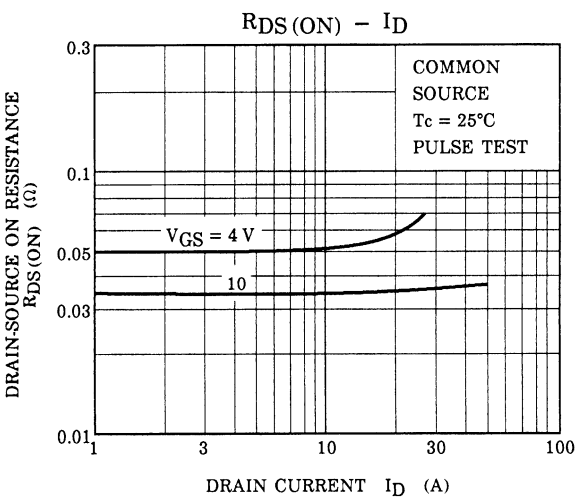
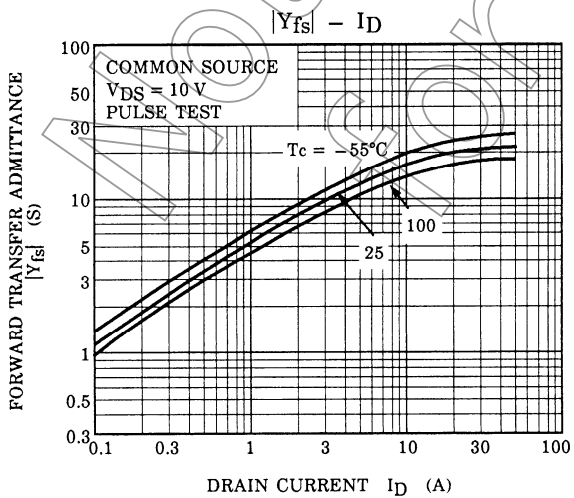
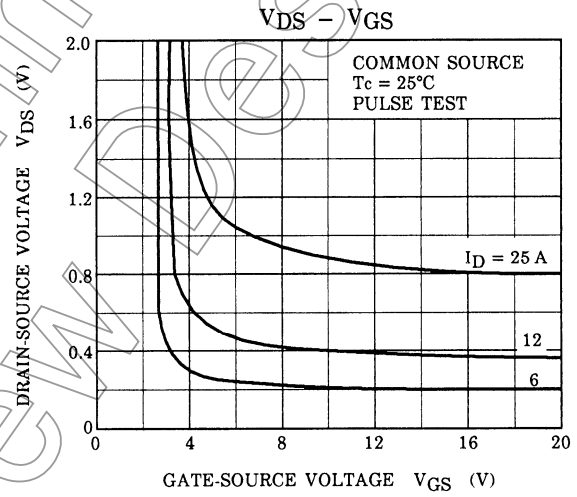
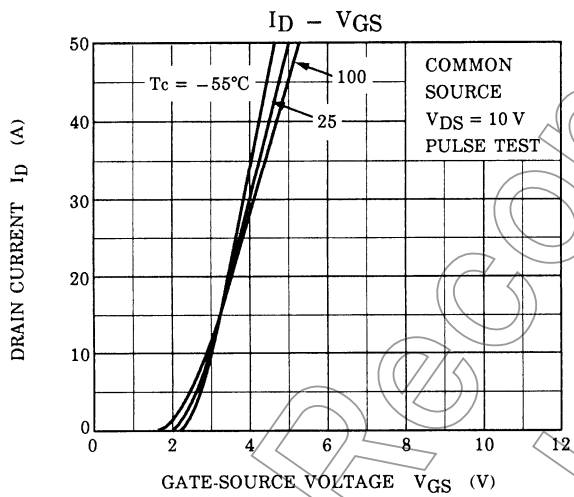
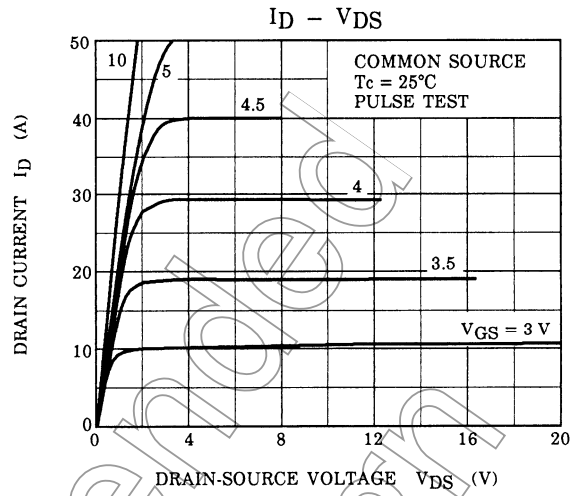
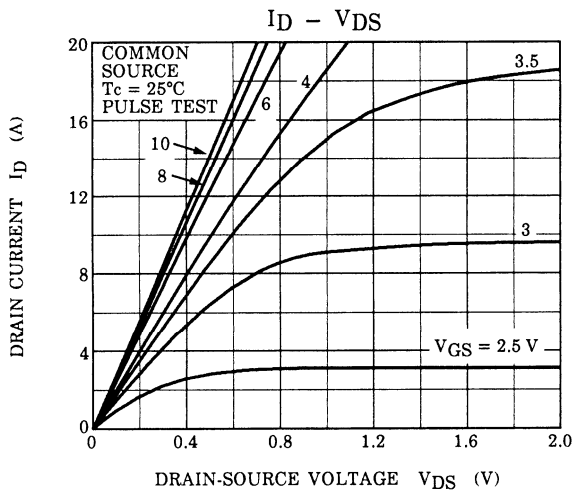


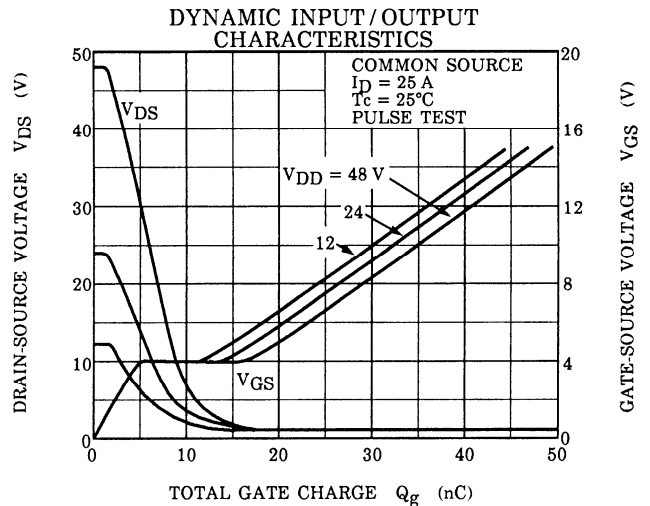
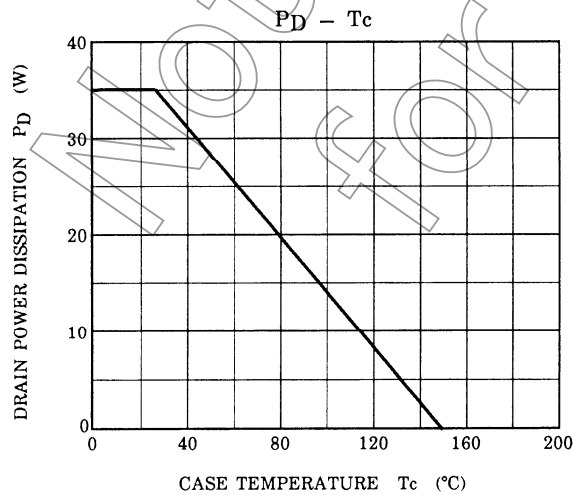
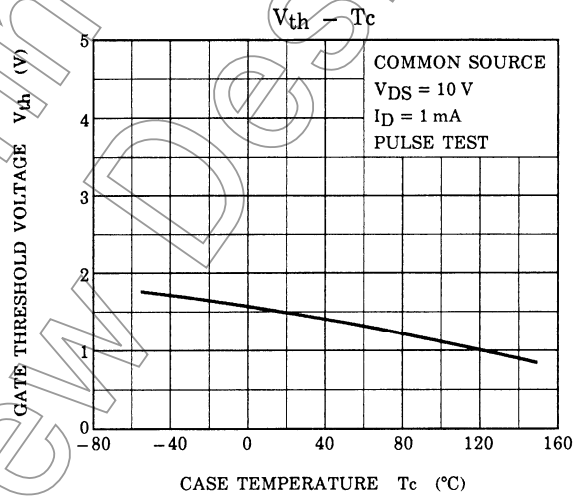
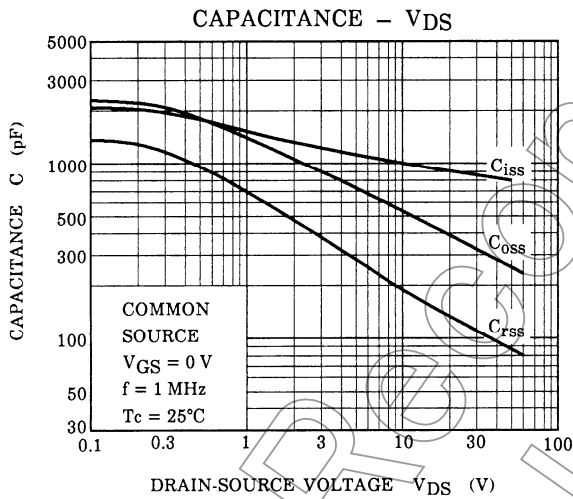
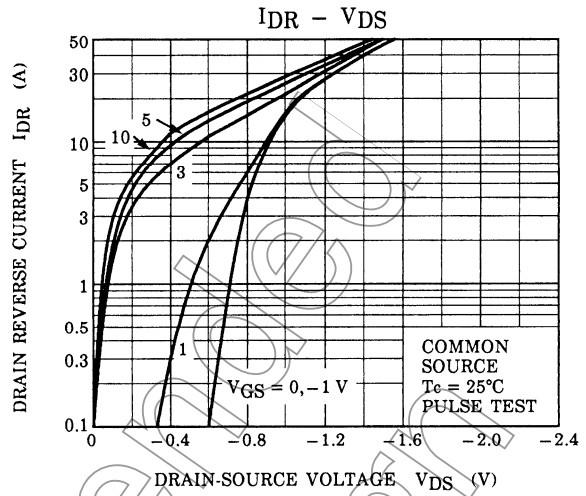
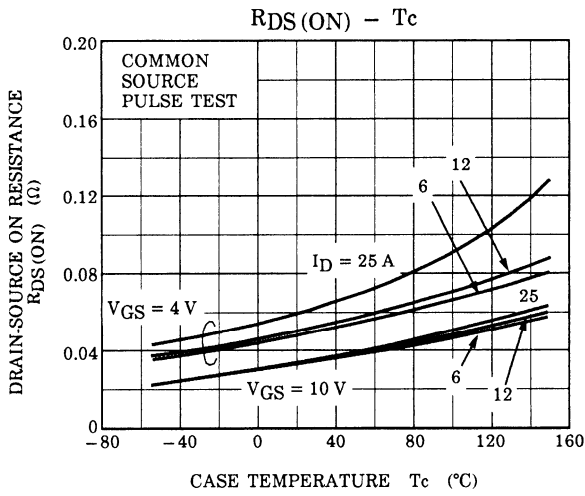
Note 4: A line under a Lot No. identifies the indication of product Labels.

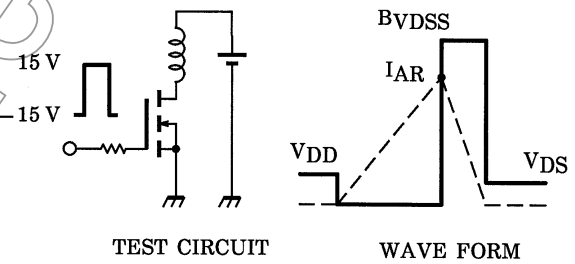
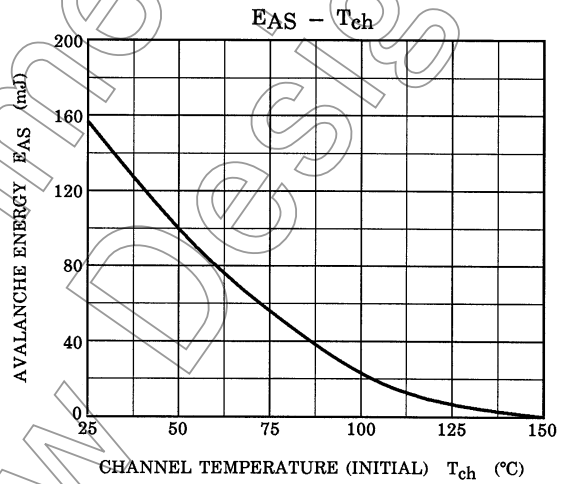
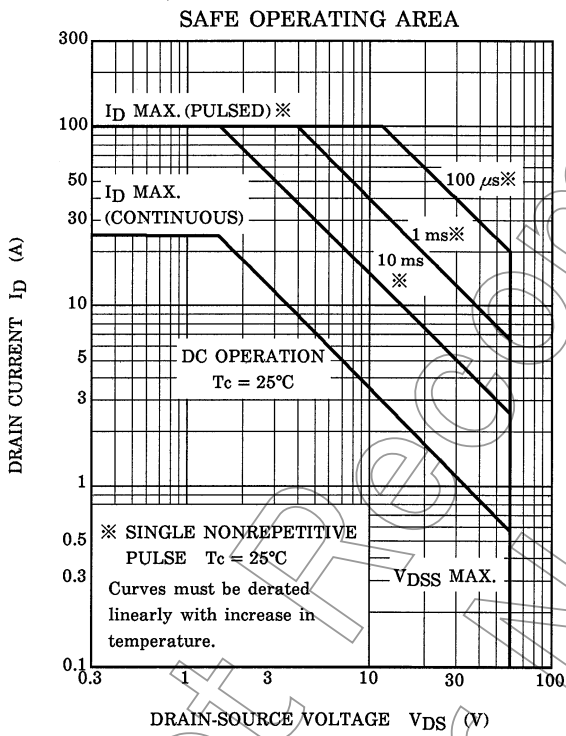
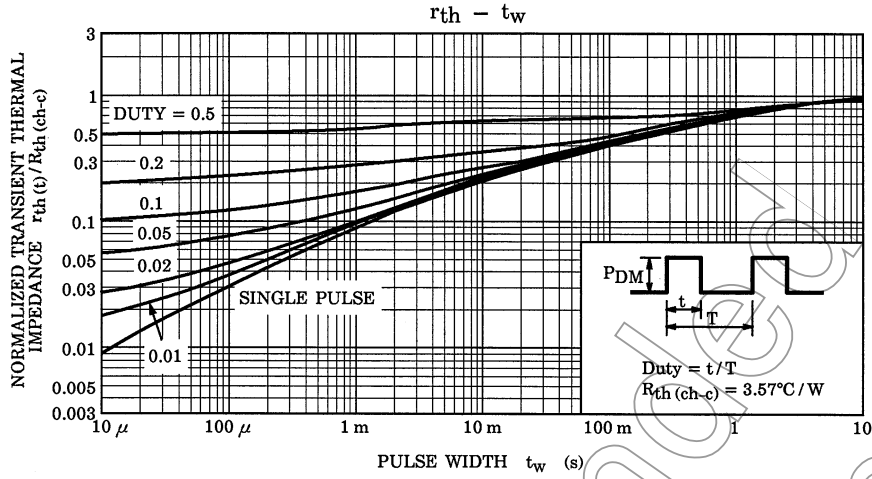
Not underlined:  $[[Pb]]/INCLUDES > MCV$

Underlined:  $[[G]]/RoHS\ COMPATIBLE$  or  $[[G]]/RoHS\ [[Pb]]$

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$R_G = 25 \Omega$   
 $V_{DD} = 25 \text{ V}, L = 339 \mu\text{H}$

$$EAS = \frac{1}{2} \cdot L \cdot I^2 \cdot \left( \frac{BVDSS}{BVDSS - V_{DD}} \right)$$

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